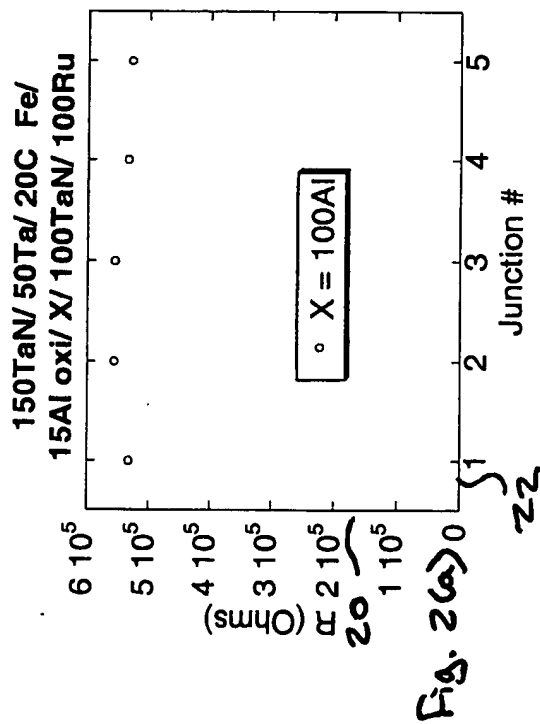


Fig. 1: TEM x-section of a stack grown for use in a resistive element array. The bottom of the stack consists of 150TaN/50Ta/20CoFe (dark area), on top of that a 15 Å Al, that were oxidized using remote plasma (smooth grey area), followed by 100 Å Al (bright contrast) and 100 Å of TaN.



- CoFe-seed layer, thin Al-barrier
- Tight clusters in Ra
- TEM shows smooth underlayer, rough Al-cap

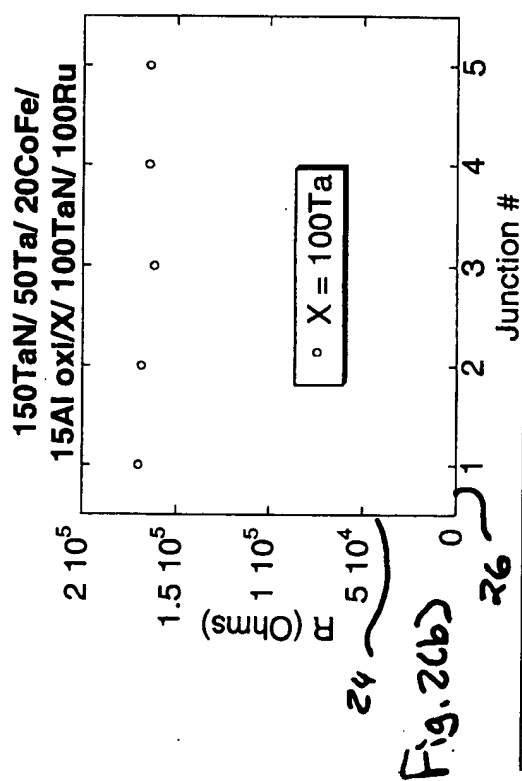
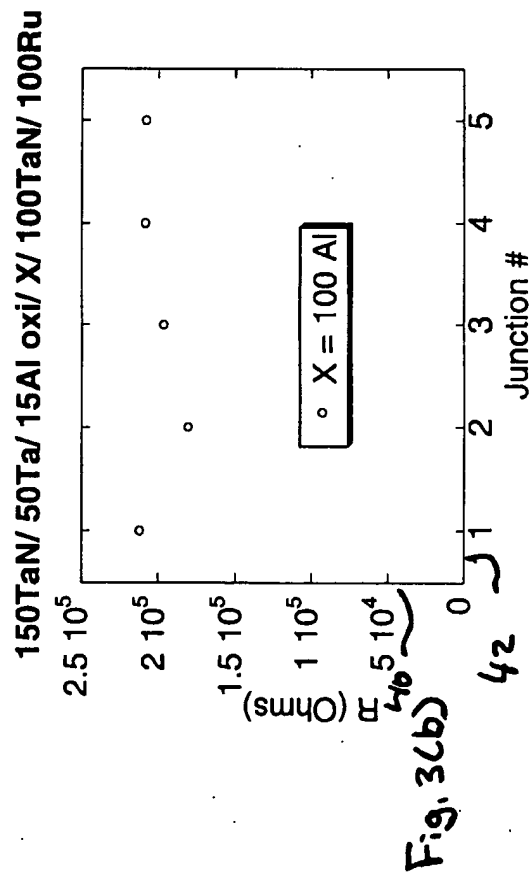
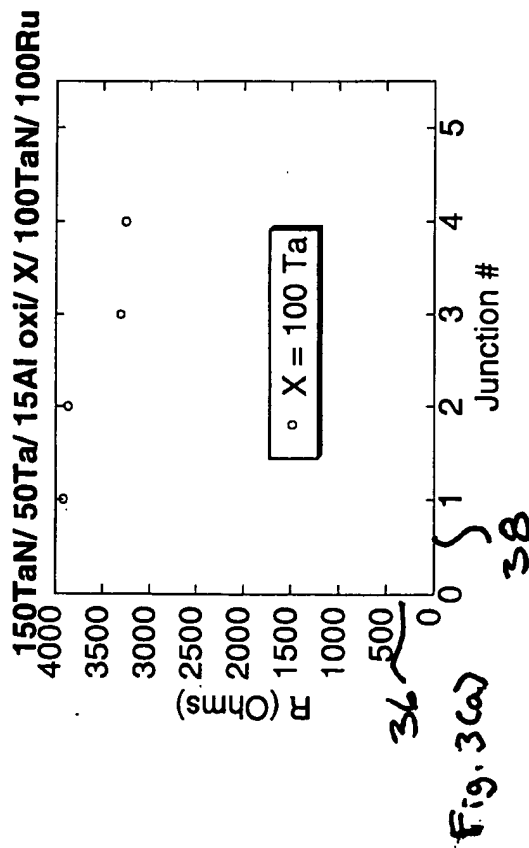


Fig. 2: Electrical data of stacks w/ CoFe-seed



- No CoFe seed, thin Al
- larger spread in Ra, indicates that CoFe-seed is beneficial

Fig. 3: Electrical data of stacks w/o CoFe-seed

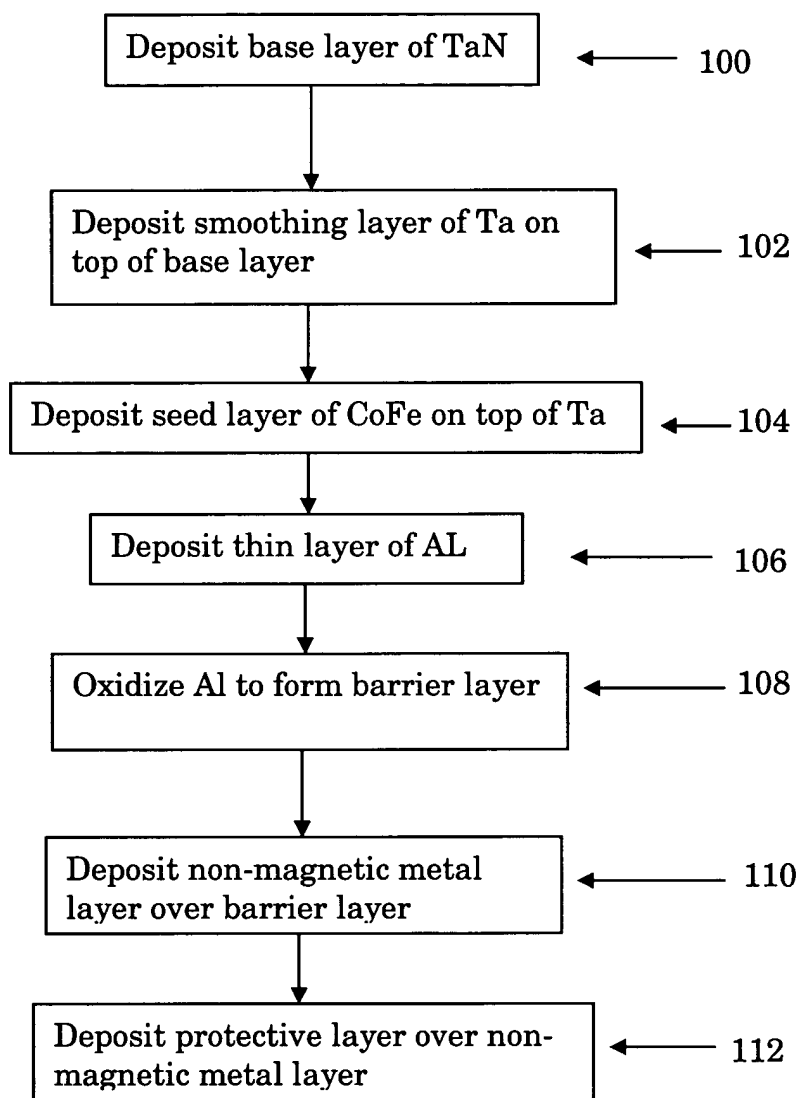


FIG. 4